

Notice of References Cited

Application/Control No.

10/726,384

Applicant(s)/Patent Under
Reexamination
OOI ET AL.

Examiner

Savitri Mulpuri

Art Unit

2812

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U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-5,395,793	03-1995	Charbonneau et al.	438/797
	B	US-2003/0096509	05-2003	Dubowski, Jan J.	438/796
	C	US-2002/0072142	06-2002	Ooi et al.	438/46
	D	US-2002/0030185	03-2002	Thompson et al.	257/14
	E	US-2004/0038503	02-2004	Fu et al.	438/511
	F	US-6,674,778	01-2004	Lin et al.	372/46
	G	US-6,632,684	10-2003	Marsh et al.	438/7
	H	US-2004/0106224	06-2004	Hamilton et al.	438/031
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Yamad et al, "strained InGaAs/GaAs a single quntum well lasers with suitable absorbers fabricated by quntum well intermixing"Appl.Phys.Lett.60(20)18 May 1992, pp2463-2465
	V	Piva et al,"Bandgap tuning semiconductor quntum well structure using ion implantation"Superlattice and Microstructures vol 15 n0. 15, 1994 pp385-389.
	W	Lbrie et l, "Effects of low tmerature prea nnaling on ion-implant assited intermixing of SiGe/Si quntum wellls, Appl. Phys. Lett 69(250december 1996
	X	Effects of doapnts in the spin-on glass layer on the bandgap shift in gaAs/alGaAs and inGaAs?alGaAs intermixing quntum wells, IEEE pp. 145-148.

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Goldberg et al,"Ion Beam intermixing of Semiconductor heterostructures for optoelectronic Applications" Nuclear Instrument and Methods in Physics Research B (127/128(1997)pp418-422.
	V	
	W	
	X	

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